

Appl. No. 09/830,598
Amdt. dated November 2, 2003
Reply to Office action of May 2, 2003

¹²
17. (currently amended) The halftone phase shift photomask blank according to any one of claims ⁸10, and ^{14, 9, 10, 11}13 to 16, which has a structure wherein an etching stopper layer is formed on the transparent substrate, with halftone phase shift films laminated successively thereon.

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concl.

¹³
18. (original) The halftone phase shift photomask blank according to claim ¹²17, which has a structure wherein halftone phase shift films are successively laminated on the etching stopper layer formed of a film composed mainly of hafnium oxide.
